Microsemi Corporation - AFS090-1FGG256I Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	27648
Number of I/O	75
Number of Gates	90000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/afs090-1fgg256i

Advanced Architecture

The proprietary Fusion architecture provides granularity comparable to standard-cell ASICs. The Fusion device consists of several distinct and programmable architectural features, including the following (Figure 1-1 on page 1-5):

- Embedded memories
  - Flash memory blocks
  - FlashROM
  - SRAM and FIFO
- Clocking resources
  - PLL and CCC
  - RC oscillator
  - Crystal oscillator
  - No-Glitch MUX (NGMUX)
- Digital I/Os with advanced I/O standards
- FPGA VersaTiles
- Analog components
  - ADC
  - Analog I/Os supporting voltage, current, and temperature monitoring
  - 1.5 V on-board voltage regulator
  - Real-time counter

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic lookup table (LUT) equivalent or a D-flip-flop or latch (with or without enable) by programming the appropriate flash switch interconnections. This versatility allows efficient use of the FPGA fabric. The VersaTile capability is unique to the Microsemi families of flash-based FPGAs. VersaTiles and larger functions are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

In addition, extensive on-chip programming circuitry allows for rapid (3.3 V) single-voltage programming of Fusion devices via an IEEE 1532 JTAG interface.

Unprecedented Integration

Integrated Analog Blocks and Analog I/Os

Fusion devices offer robust and flexible analog mixed signal capability in addition to the high-performance flash FPGA fabric and flash memory block. The many built-in analog peripherals include a configurable 32:1 input analog MUX, up to 10 independent MOSFET gate driver outputs, and a configurable ADC. The ADC supports 8-, 10-, and 12-bit modes of operation with a cumulative sample rate up to 600 k samples per second (Ksps), differential nonlinearity (DNL) < 1.0 LSB, and Total Unadjusted Error (TUE) of 0.72 LSB in 10-bit mode. The TUE is used for characterization of the conversion error and includes errors from all sources, such as offset and linearity. Internal bandgap circuitry offers 1% voltage reference accuracy with the flexibility of utilizing an external reference voltage. The ADC channel sampling sequence and sampling rate are programmable and implemented in the FPGA logic using Designer and Libero SoC software tool support.

Two channels of the 32-channel ADCMUX are dedicated. Channel 0 is connected internally to VCC and can be used to monitor core power supply. Channel 31 is connected to an internal temperature diode which can be used to monitor device temperature. The 30 remaining channels can be connected to external analog signals. The exact number of I/Os available for external connection signals is device-dependent (refer to the "Fusion Family" table on page I for details).

VersaNet Global Networks and Spine Access

The Fusion architecture contains a total of 18 segmented global networks that can access the VersaTiles, SRAM, and I/O tiles on the Fusion device. There are 6 chip (main) global networks that access the entire device and 12 quadrant networks (3 in each quadrant). Each device has a total of 18 globals. These VersaNet global networks offer fast, low-skew routing resources for high-fanout nets, including clock signals. In addition, these highly segmented global networks offer users the flexibility to create low-skew local networks using spines for up to 180 internal/external clocks (in an AFS1500 device) or other high-fanout nets in Fusion devices. Optimal usage of these low-skew networks can result in significant improvement in design performance on Fusion devices.

The nine spines available in a vertical column reside in global networks with two separate regions of scope: the quadrant global network, which has three spines, and the chip (main) global network, which has six spines. Note that there are three quadrant spines in each quadrant of the device. There are four quadrant global network regions per device (Figure 2-12 on page 2-12).

The spines are the vertical branches of the global network tree, shown in Figure 2-11 on page 2-11. Each spine in a vertical column of a chip (main) global network is further divided into two equal-length spine segments: one in the top and one in the bottom half of the die.

Each spine and its associated ribs cover a certain area of the Fusion device (the "scope" of the spine; see Figure 2-11 on page 2-11). Each spine is accessed by the dedicated global network MUX tree architecture, which defines how a particular spine is driven—either by the signal on the global network from a CCC, for example, or another net defined by the user (Figure 2-13). Quadrant spines can be driven from user I/Os on the north and south sides of the die, via analog I/Os configured as direct digital inputs. The ability to drive spines in the quadrant global networks can have a significant effect on system performance for high-fanout inputs to a design.

Details of the chip (main) global network spine-selection MUX are presented in Figure 2-13. The spine drivers for each spine are located in the middle of the die.

Quadrant spines are driven from a north or south rib. Access to the top and bottom ribs is from the corner CCC or from the I/Os on the north and south sides of the device. For details on using spines in Fusion devices, see the application note *Using Global Resources in Actel Fusion Devices*.

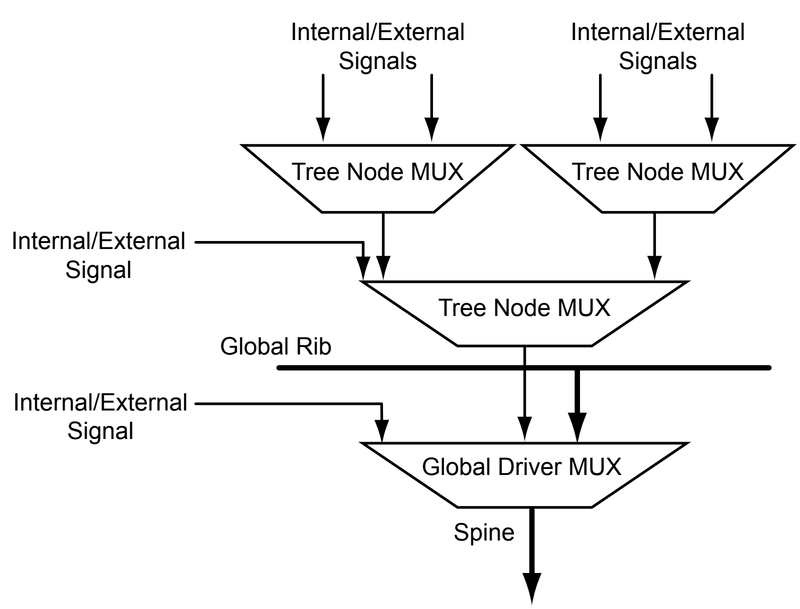


Figure 2-13 **• Spine-Selection MUX of Global Tree**

Clock Aggregation

Clock aggregation allows for multi-spine clock domains. A MUX tree provides the necessary flexibility to allow long lines or I/Os to access domains of one, two, or four global spines. Signal access to the clock aggregation system is achieved through long-line resources in the central rib, and also through local resources in the north and south ribs, allowing I/Os to feed directly into the clock system. As Figure 2-14 indicates, this access system is contiguous.

There is no break in the middle of the chip for north and south I/O VersaNet access. This is different from the quadrant clocks, located in these ribs, which only reach the middle of the rib. Refer to the *Using Global Resources in Actel Fusion Devices* application note.

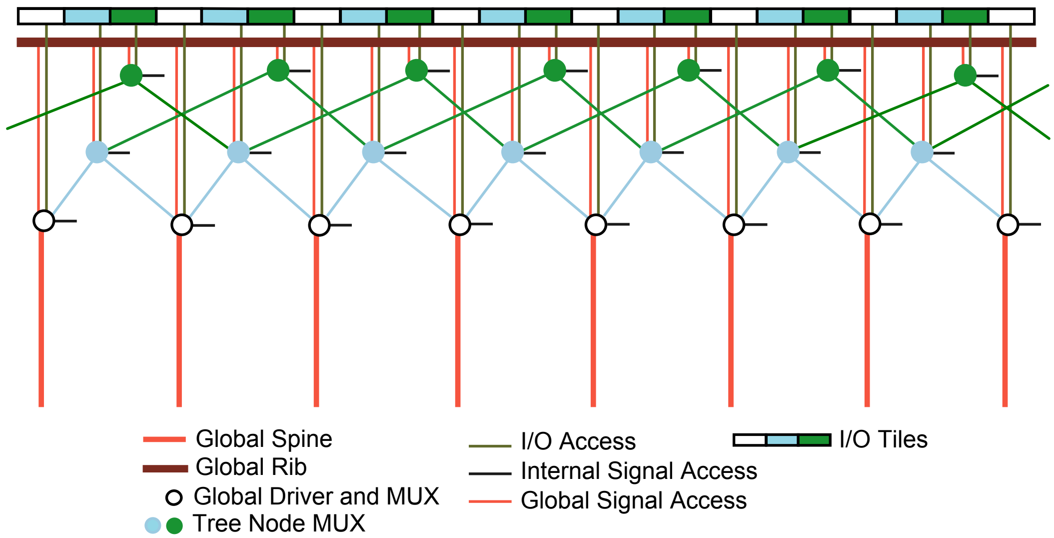


Figure 2-14 • **Clock Aggregation Tree Architecture**

Modes of Operation

Standby Mode

Standby mode allows periodic power-up and power-down of the FPGA fabric. In standby mode, the real-time counter and crystal block are ON. The FPGA is not powered by disabling the 1.5 V voltage regulator. The 1.5 V voltage regulator can be enabled when the preset count is matched. Refer to the "Real-Time Counter (part of AB macro)" section for details. To enter standby mode, the RTC must be first configured and enabled. Then VRPSM is shut off by deasserting the VRPU signal. The 1.5 V voltage regulator is then disabled, and shuts off the 1.5 V output.

Sleep Mode

In sleep mode, the real-time counter and crystal blocks are OFF. The 1.5 V voltage regulator inside the VRPSM can only be enabled by the PUB or TRST pin. Refer to the "Voltage Regulator and Power System Monitor (VRPSM)" section on page 2-36 for details on power-up and power-down of the 1.5 V voltage regulator.

Standby and Sleep Mode Circuit Implementation

For extra power savings, VJTAG and VPUMP should be at the same voltage as VCC, floated or ground, during standby and sleep modes. Note that when VJTAG is not powered, the 1.5 V voltage regulator cannot be enabled through TRST.

VPUMP and VJTAG can be controlled through an external switch. Microsemi recommends ADG839, ADG849, or ADG841 as possible switches. Figure 2-28 shows the implementation for controlling VPUMP. The IN signal of the switch can be connected to PTBASE of the Fusion device. VJTAG can be controlled in same manner.

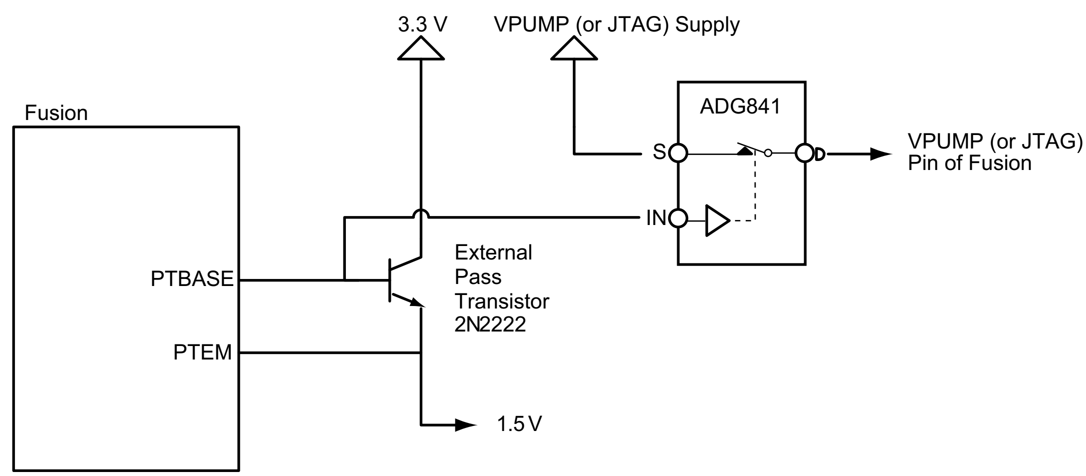


***Figure 2-28 •* Implementation to Control VPUMP**

Flash Memory Block Pin Names

***Table 2-19* • Flash Memory Block Pin Names**

Interface Name	Width	Direction	Description
ADDR[17:0]	18	In	Byte offset into the FB. Byte-based address.
AUXBLOCK	1	In	When asserted, the page addressed is used to access the auxiliary block within that page.
BUSY	1	Out	When asserted, indicates that the FB is performing an operation.
CLK	1	In	User interface clock. All operations and status are synchronous to the rising edge of this clock.
DATAWIDTH[1:0]	2	In	Data width 00 = 1 byte in RD/WD[7:0] 01 = 2 bytes in RD/WD[15:0] 1x = 4 bytes in RD/WD[31:0]
DISCARDPAGE	1	In	When asserted, the contents of the Page Buffer are discarded so that a new page write can be started.
ERASEPAGE	1	In	When asserted, the address page is to be programmed with all zeros. ERASEPAGE must transition synchronously with the rising edge of CLK.
LOCKREQUEST	1	In	When asserted, indicates to the JTAG controller that the FPGA interface is accessing the FB.
OVERWRITEPAGE	1	In	When asserted, the page addressed is overwritten with the contents of the Page Buffer if the page is writable.
OVERWRITEPROTECT	1	In	When asserted, all program operations will set the overwrite protect bit of the page being programmed.
PAGESTATUS	1	In	When asserted with REN, initiates a read page status operation.
PAGELOSSPROTECT	1	In	When asserted, a modified Page Buffer must be programmed or discarded before accessing a new page.
PIPE	1	In	Adds a pipeline stage to the output for operation above 50 MHz.
PROGRAM	1	In	When asserted, writes the contents of the Page Buffer into the FB page addressed.
RD[31:0]	32	Out	Read data; data will be valid from the first non-busy cycle (BUSY = 0) after REN has been asserted.
READNEXT	1	In	When asserted with REN, initiates a read-next operation.
REN	1	In	When asserted, initiates a read operation.
RESET	1	In	When asserted, resets the state of the FB (active low).
SPAREPAGE	1	In	When asserted, the sector addressed is used to access the spare page within that sector.

The AEMPTY flag is asserted when the difference between the write address and the read address is less than a predefined value. In the example above, a value of 200 for AEVAL means that the AEMPTY flag will be asserted when a read causes the difference between the write address and the read address to drop to 200. It will stay asserted until that difference rises above 200. Note that the FIFO can be configured with different read and write widths; in this case, the AFVAL setting is based on the number of write data entries and the AEVAL setting is based on the number of read data entries. For aspect ratios of 512×9 and 256×18, only 4,096 bits can be addressed by the 12 bits of AFVAL and AEVAL. The number of words must be multiplied by 8 and 16, instead of 9 and 18. The SmartGen tool automatically uses the proper values. To avoid halfwords being written or read, which could happen if different read and write aspect ratios are specified, the FIFO will assert FULL or EMPTY as soon as at least a minimum of one word cannot be written or read. For example, if a two-bit word is written and a four-bit word is being read, the FIFO will remain in the empty state when the first word is written. This occurs even if the FIFO is not completely empty, because in this case, a complete word cannot be read. The same is applicable in the full state. If a four-bit word is written and a two-bit word is read, the FIFO is full and one word is read. The FULL flag will remain asserted because a complete word cannot be written at this point.

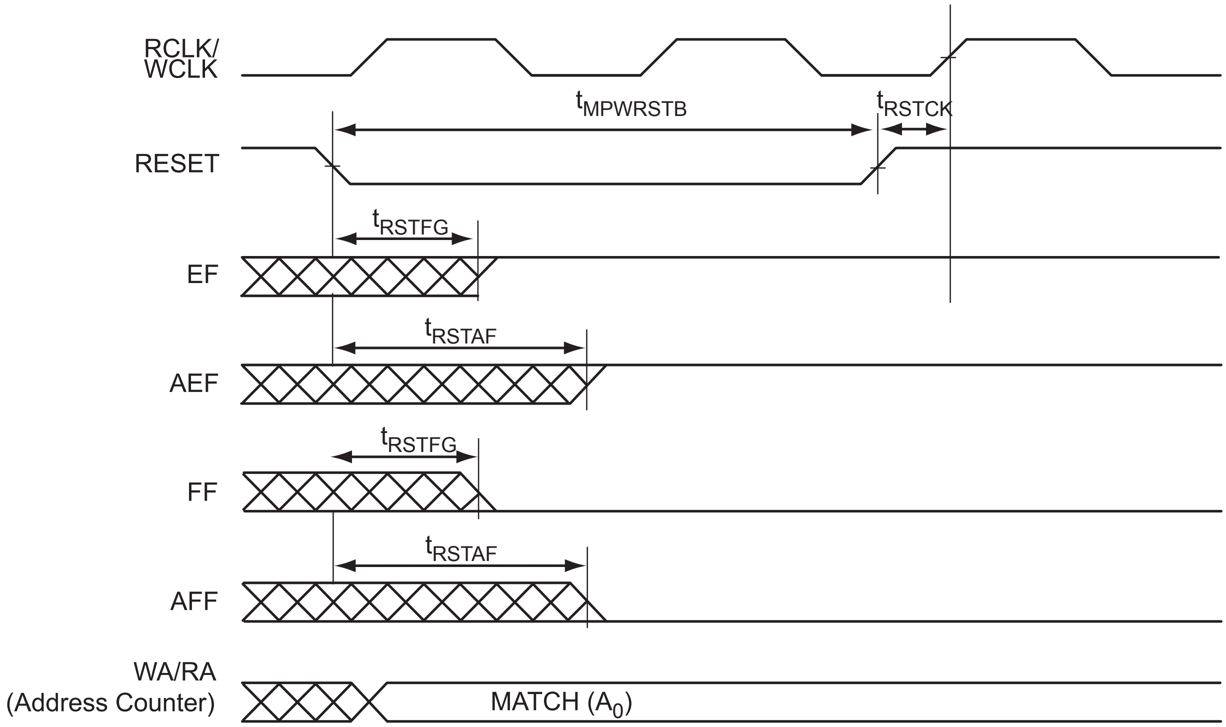


Figure 2-59 • **FIFO Reset**

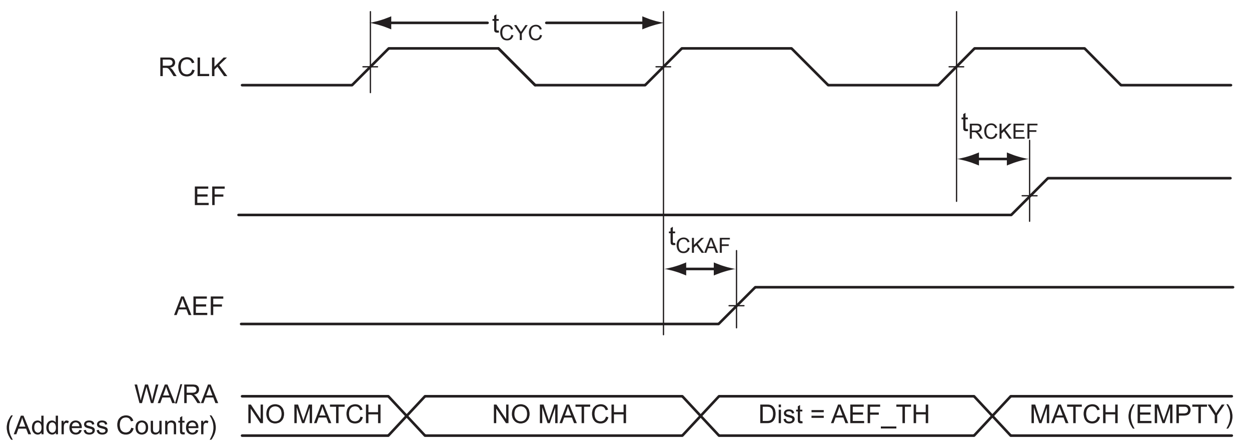


Figure 2-60 • **FIFO EMPTY Flag and AEMPTY Flag Assertion**

The diode's voltage is measured at each current level and the temperature is calculated based on EQ 7.

$$V_{\text{TMSLO}} - V_{\text{TMSHI}} = n\frac{kT}{q}\left(\ln\frac{I_{\text{TMSLO}}}{I_{\text{TMSHI}}}\right)$$

EQ 7

where

I_{TMSLO} is the current when the Temperature Strobe is Low, typically 100 µA

I_{TMSHI} is the current when the Temperature Strobe is High, typically 10 µA

V_{TMSLO} is diode voltage while Temperature Strobe is Low

V_{TMSHI} is diode voltage while Temperature Strobe is High

n is the non-ideality factor of the diode-connected transistor. It is typically 1.004 for the Microsemi-recommended transistor type 2N3904.

$K = 1.3806 \times 10^{-23}$ J/K is the Boltzman constant

$Q = 1.602 \times 10^{-19}$ C is the charge of a proton

When $I_{TMSLO} / I_{TMSHI} = 10$, the equation can be simplified as shown in EQ 8.

$$\Delta V = V_{\text{TMSLO}} - V_{\text{TMSHI}} = 1.986 \times 10^{-4} nT$$

EQ 8

In the Fusion TMB, the ideality factor n for 2N3904 is 1.004 and ΔV is amplified 12.5 times by an internal amplifier; hence the voltage before entering the ADC is as given in EQ 9.

$$V_{ADC} = \Delta V \times 12.5 = 2.5\ \text{mV} / (K \times T)$$

EQ 9

This means the temperature to voltage relationship is 2.5 mV per degree Kelvin. The unique design of Fusion has made the Temperature Monitor System simple for the user. When the 10-bit mode ADC is used, each LSB represents 1 degree Kelvin, as shown in EQ 10. That is, e. 25°C is equal to 293°K and is represented by decimal 293 counts from the ADC.

$$1K = 2.5\ \text{mV} \times \frac{2^{10}}{2.56\ \text{V}} = 1\ \text{LSB}$$

EQ 10

If 8-bit mode is used for the ADC resolution, each LSB represents 4 degrees Kelvin; however, the resolution remains as 1 degree Kelvin per LSB, even for 12-bit mode, due to the Temperature Monitor design. An example of the temperature data format for 10-bit mode is shown in Table 2-38.

Table 2-38 **• Temperature Data Format**

Temperature	Temperature (K)	Digital Output (ADC 10-bit mode)
–40°C	233	00 1110 1001
–20°C	253	00 1111 1101
0°C	273	01 0001 0001
1°C	274	01 0001 0010
10 °C	283	01 0001 1011
25°C	298	01 0010 1010
50 °C	323	01 0100 0011
85 °C	358	01 0110 0110

Table 2-50 **• ADC Characteristics in Direct Input Mode**
Commercial Temperature Range Conditions, T_J = 85°C (unless noted otherwise),
Typical: VCC33A = 3.3 V, VCC = 1.5 V

Parameter	Description	Condition	Min.	Typ.	Max.	Units
Direct Input using Analog Pad AV, AC, AT						
VINADC	Input Voltage (Direct Input)	Refer to Table 3-2 on page 3-3				
CINADC	Input Capacitance	Channel not selected		7		pF
		Channel selected but not sampling		8		pF
		Channel selected and sampling		18		pF
ZINADC	Input Impedance	8-bit mode		2		kΩ
		10-bit mode		2		kΩ
		12-bit mode		2		kΩ
Analog Reference Voltage VAREF						
VAREF	Accuracy	T_J = 25°C	2.537	2.56	2.583	V
	Temperature Drift of Internal Reference			65		ppm / °C
	External Reference		2.527		VCC33A + 0.05	V
ADC Accuracy (using external reference) [1,2]						
DC Accuracy						
TUE	Total Unadjusted Error	8-bit mode	0.29			LSB
		10-bit mode	0.72			LSB
		12-bit mode	1.8			LSB
INL	Integral Non-Linearity	8-bit mode		0.20	0.25	LSB
		10-bit mode		0.32	0.43	LSB
		12-bit mode		1.71	1.80	LSB
DNL	Differential Non-Linearity (no missing code)	8-bit mode		0.20	0.24	LSB
		10-bit mode		0.60	0.65	LSB
		12-bit mode		2.40	2.48	LSB
	Offset Error	8-bit mode		0.01	0.17	LSB
		10-bit mode		0.05	0.20	LSB
		12-bit mode		0.20	0.40	LSB
	Gain Error	8-bit mode		0.0004	0.003	LSB
		10-bit mode		0.002	0.011	LSB
		12-bit mode		0.007	0.044	LSB
	Gain Error (with internal reference)	All modes		2		% FSR

Notes:

1. *Accuracy of the external reference is 2.56 V ± 4.6 mV.*
2. *Data is based on characterization.*
3. *The sample rate is time-shared among active analog inputs.*

Table 2-53 • Analog Channel Accuracy: Monitoring Standard Positive Voltages
Typical Conditions, T_A = 25°C

Input Voltage (V)	Calibrated Typical Error per Positive Prescaler Setting [1] (%FSR)							Direct ADC [2,3] (%FSR)
	16 V (AT)	16 V (12 V) (AV/AC)	8 V (AV/AC)	4 V (AT)	4 V (AV/AC)	2 V (AV/AC)	1 V (AV/AC)	VAREF = 2.56 V
15	1							
14	1							
12	1	1						
5	2	2	1					
3.3	2	2	1	1	1			
2.5	3	2	1	1	1			1
1.8	4	4	1	1	1	1		1
1.5	5	5	2	2	2	1		1
1.2	7	6	2	2	2	1		1
0.9	9	9	4	3	3	1	1	1

Notes:

1. *Requires enabling Analog Calibration using SmartGen Analog System Builder. For further details, refer to the "Temperature, Voltage, and Current Calibration in Fusion FPGAs" chapter of the Fusion FPGA Fabric User Guide.*
2. *Direct ADC mode using an external VAREF of 2.56V±4.6mV, without Analog Calibration macro.*
3. *For input greater than 2.56 V, the ADC output will saturate. A higher VAREF or prescaler usage is recommended.*

Examples

Calculating Accuracy for an Uncalibrated Analog Channel

Formula

For a given prescaler range, EQ 30 gives the output voltage.

Output Voltage = (Channel Output Offset in V) + (Input Voltage x Channel Gain)

EQ 30

where

Channel Output offset in V = Channel Input offset in LSBs x Equivalent voltage per LSB

Channel Gain Factor = 1+ (% Channel Gain / 100)

Example

Input Voltage = 5 V

Chosen Prescaler range = 8 V range

Refer to Table 2-51 on page 2-122.

Max. Output Voltage = (Max Positive input offset) + (Input Voltage x Max Positive Channel Gain)

Max. Positive input offset = (21 LSB) x (8 mV per LSB in 10-bit mode)

Max. Positive input offset = 166 mV

Max. Positive Gain Error = +3%

Max. Positive Channel Gain = 1 + (+3% / 100)

Max. Positive Channel Gain = 1.03

Max. Output Voltage = (166 mV) + (5 V x 1.03)

Max. Output Voltage = **5.316 V**

Temporary overshoots are allowed according to Table 3-4 on page 3-4.

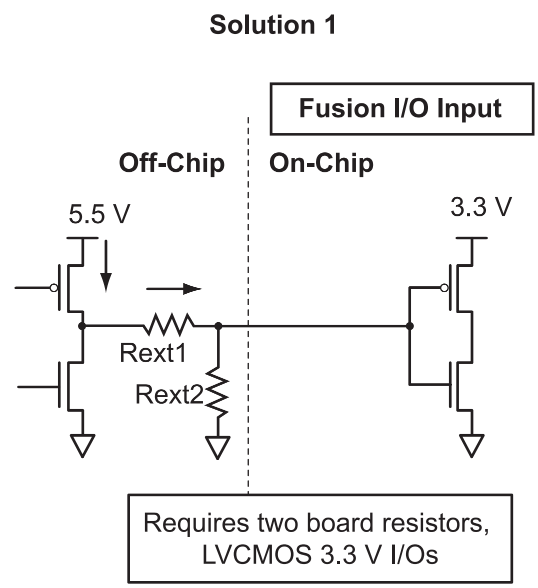


Figure 2-103 • **Solution 1**

Solution 2

The board-level design must ensure that the reflected waveform at the pad does not exceed limits provided in Table 3-4 on page 3-4. This is a long-term reliability requirement.

This scheme will also work for a 3.3 V PCI/PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the external resistors and Zener, as shown in Figure 2-104. Relying on the diode clamping would create an excessive pad DC voltage of 3.3 V + 0.7 V = 4 V.

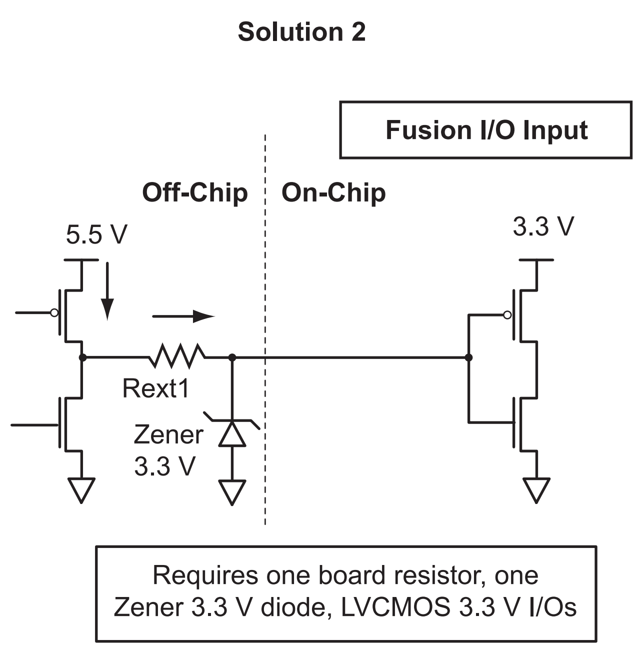


Figure 2-104 • **Solution 2**

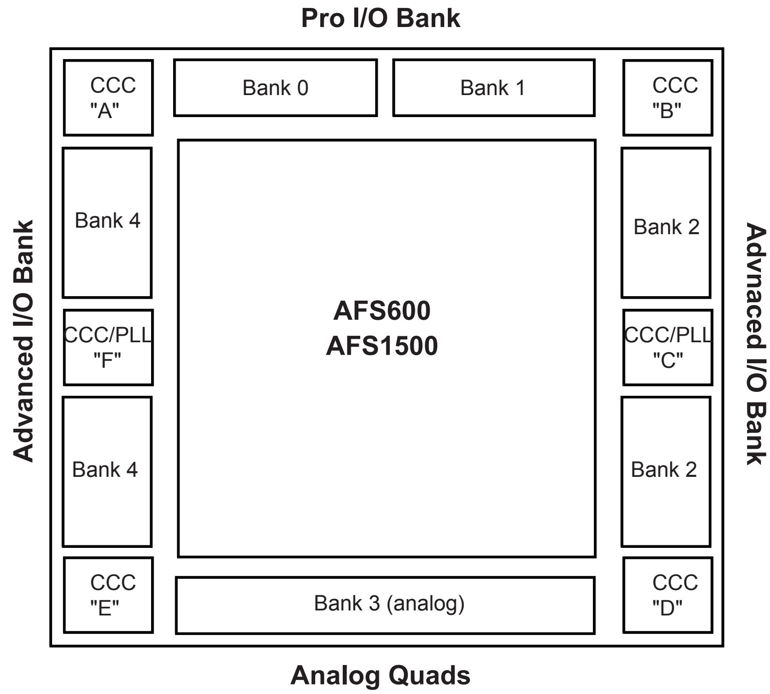


Figure 2-114 • **Naming Conventions of Fusion Devices with Four I/O Banks**

***Table 2-130* • 1.5 V LVCMOS Low Slew**
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	12.78	0.04	1.31	0.43	12.81	12.78	3.40	2.64	15.05	15.02	ns
	–1	0.56	10.87	0.04	1.11	0.36	10.90	10.87	2.89	2.25	12.80	12.78	ns
	–2	0.49	9.55	0.03	0.98	0.32	9.57	9.55	2.54	1.97	11.24	11.22	ns
4 mA	Std.	0.66	10.01	0.04	1.31	0.43	10.19	9.55	3.75	3.27	12.43	11.78	ns
	–1	0.56	8.51	0.04	1.11	0.36	8.67	8.12	3.19	2.78	10.57	10.02	ns
	–2	0.49	7.47	0.03	0.98	0.32	7.61	7.13	2.80	2.44	9.28	8.80	ns
8 mA	Std.	0.66	9.33	0.04	1.31	0.43	9.51	8.89	3.83	3.43	11.74	11.13	ns
	–1	0.56	7.94	0.04	1.11	0.36	8.09	7.56	3.26	2.92	9.99	9.47	ns
	–2	0.49	6.97	0.03	0.98	0.32	7.10	6.64	2.86	2.56	8.77	8.31	ns
12 mA	Std.	0.66	8.91	0.04	1.31	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	–1	0.56	7.58	0.04	1.11	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	–2	0.49	6.65	0.03	0.98	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.

***Table 2-131* • 1.5 V LVCMOS High Slew**
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	8.36	0.04	1.44	0.43	6.82	8.36	3.39	2.77	9.06	10.60	ns
	–1	0.56	7.11	0.04	1.22	0.36	5.80	7.11	2.88	2.35	7.71	9.02	ns
	–2	0.49	6.24	0.03	1.07	0.32	5.10	6.24	2.53	2.06	6.76	7.91	ns
4 mA	Std.	0.66	5.31	0.04	1.44	0.43	4.85	5.31	3.74	3.40	7.09	7.55	ns
	–1	0.56	4.52	0.04	1.22	0.36	4.13	4.52	3.18	2.89	6.03	6.42	ns
	–2	0.49	3.97	0.03	1.07	0.32	3.62	3.97	2.79	2.54	5.29	5.64	ns
8 mA	Std.	0.66	4.67	0.04	1.44	0.43	4.55	4.67	3.82	3.56	6.78	6.90	ns
	–1	0.56	3.97	0.04	1.22	0.36	3.87	3.97	3.25	3.03	5.77	5.87	ns
	–2	0.49	3.49	0.03	1.07	0.32	3.40	3.49	2.85	2.66	5.07	5.16	ns
12 mA	Std.	0.66	4.08	0.04	1.44	0.43	4.15	3.58	3.94	4.20	6.39	5.81	ns
	–1	0.56	3.47	0.04	1.22	0.36	3.53	3.04	3.36	3.58	5.44	4.95	ns
	–2	0.49	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.

I/O Register Specifications

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

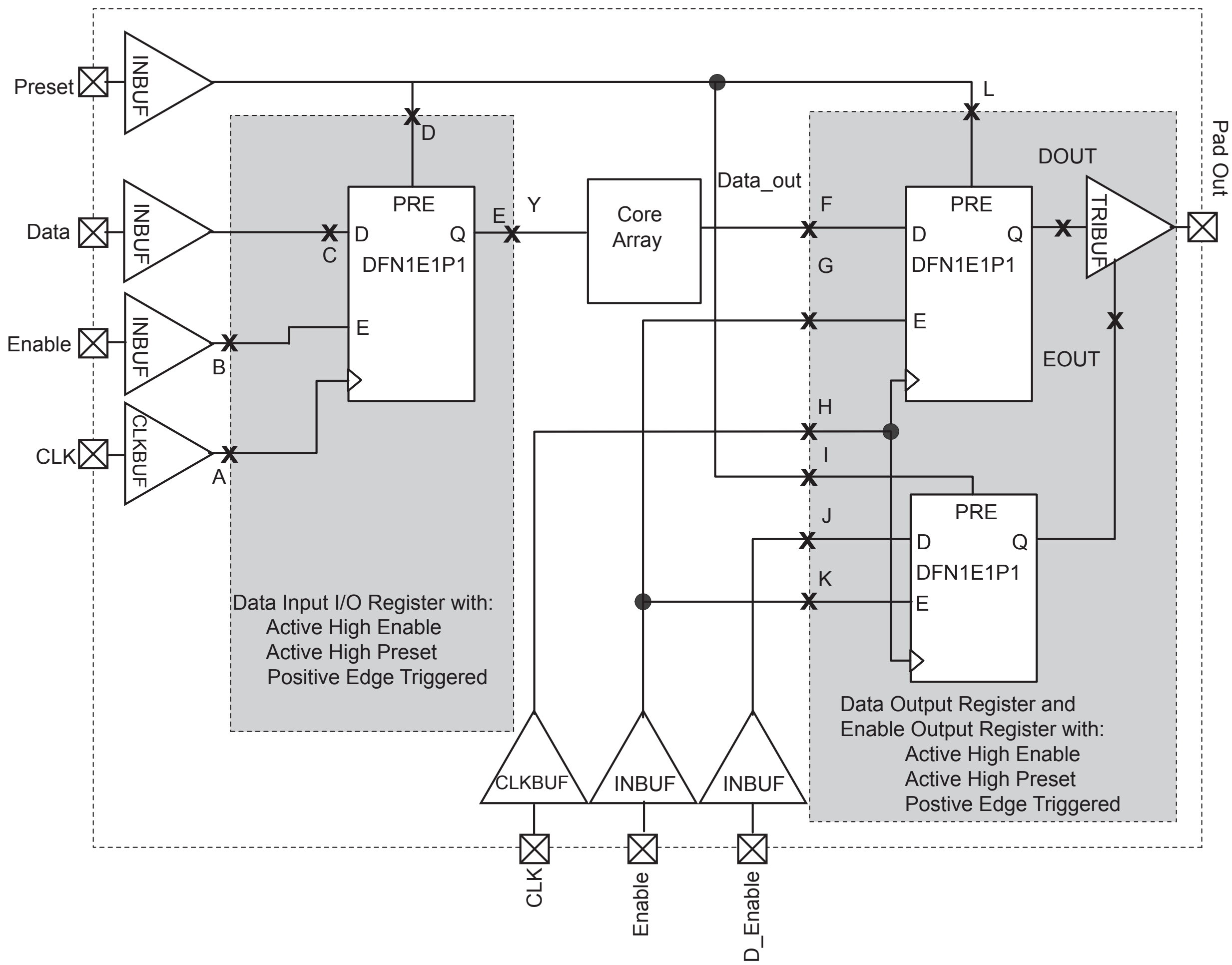


Figure 2-137 • Timing Model of Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

User-Defined Supply Pins

VREF I/O Voltage Reference

Reference voltage for I/O minibanks. Both AFS600 and AFS1500 (north bank only) support Microsemi Pro I/O. These I/O banks support voltage reference standard I/O. The VREF pins are configured by the user from regular I/Os, and any I/O in a bank, except JTAG I/Os, can be designated as the voltage reference I/O. Only certain I/O standards require a voltage reference—HSTL (I) and (II), SSTL2 (I) and (II), SSTL3 (I) and (II), and GTL/GTL+. One VREF pin can support the number of I/Os available in its minibank.

VAREF Analog Reference Voltage

The Fusion device can be configured to generate a 2.56 V internal reference voltage that can be used by the ADC. While using the internal reference, the reference voltage is output on the VAREF pin for use as a system reference. If a different reference voltage is required, it can be supplied by an external source and applied to this pin. The valid range of values that can be supplied to the ADC is 1.0 V to 3.3 V. When VAREF is internally generated by the Fusion device, a bypass capacitor must be connected from this pin to ground. The value of the bypass capacitor should be between 3.3 μF and 22 μF, which is based on the needs of the individual designs. The choice of the capacitor value has an impact on the settling time it takes the VAREF signal to reach the required specification of 2.56 V to initiate valid conversions by the ADC. If the lower capacitor value is chosen, the settling time required for VAREF to achieve 2.56 V will be shorter than when selecting the larger capacitor value. The above range of capacitor values supports the accuracy specification of the ADC, which is detailed in the datasheet. Designers choosing the smaller capacitor value will not obtain as much margin in the accuracy as that achieved with a larger capacitor value. Depending on the capacitor value selected in the Analog System Builder, a tool in Libero SoC, an automatic delay circuit will be generated using logic tiles available within the FPGA to ensure that VAREF has achieved the 2.56 V value. Microsemi recommends customers use 10 μF as the value of the bypass capacitor. Designers choosing to use an external VAREF need to ensure that a stable and clean VAREF source is supplied to the VAREF pin before initiating conversions by the ADC. Designers should also make sure that the ADCRESET signal is deasserted before initiating valid conversions.[2]

If the user connects VAREF to external 3.3 V on their board, the internal VAREF driving OpAmp tries to bring the pin down to the nominal 2.56 V until the device is programmed and up/functional. Under this scenario, it is recommended to connect an external 3.3 V supply through a ~1 KOhm resistor to limit current, along with placing a 10-100nF capacitor between VAREF and GNDA.

User Pins

I/O User Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected. Unused I/O pins are configured as inputs with pull-up resistors.

During programming, I/Os become tristated and weakly pulled up to VCCI. With the VCCI and VCC supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os get instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

A*xy* Analog Input/Output

Analog I/O pin, where *x* is the analog pad type (C = current pad, G = Gate driver pad, T = Temperature pad, V = Voltage pad) and *y* is the Analog Quad number (0 to 9). There is a minimum 1 MΩ to ground on AV, AC, and AT. This pin can be left floating when it is unused.

2. The ADC is functional with an external reference down to 1V, however to meet the performance parameters highlighted in the datasheet refer to the VAREF specification in Table 3-2 on page 3-3.

Methodology

Total Power Consumption—P_{TOTAL}

Operating Mode, Standby Mode, and Sleep Mode

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

Operating Mode

$P_{STAT} = PDC1 + (N_{NVM\text{-}BLOCKS} * PDC4) + PDC5 + (N_{QUADS} * PDC6) + (N_{INPUTS} * PDC7) + (N_{OUTPUTS} * PDC8) + (N_{PLLS} * PDC9)$

$N_{NVM\text{-}BLOCKS}$ is the number of NVM blocks available in the device.

N_{QUADS} is the number of Analog Quads used in the design.

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

N_{PLLS} is the number of PLLs available in the device.

Standby Mode

$P_{STAT} = PDC2$

Sleep Mode

$P_{STAT} = PDC3$

Total Dynamic Power Consumption—P_{DYN}

Operating Mode

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL} + P_{NVM} + P_{XTL\text{-}OSC} + P_{RC\text{-}OSC} + P_{AB}$

Standby Mode

$P_{DYN} = P_{XTL\text{-}OSC}$

Sleep Mode

$P_{DYN} = 0$ W

Global Clock Dynamic Contribution—P_{CLOCK}

Operating Mode

$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S\text{-}CELL} * PAC4) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *Fusion and Extended Temperature Fusion FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *Fusion and Extended Temperature Fusion FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

Standby Mode and Sleep Mode

$P_{CLOCK} = 0$ W

Sequential Cells Dynamic Contribution—$P_{S\text{-}CELL}$

Operating Mode

RC Oscillator Dynamic Contribution—$P_{RC\text{-}OSC}$

Operating Mode

$P_{RC\text{-}OSC}$ = PAC19

Standby Mode and Sleep Mode

$P_{RC\text{-}OSC}$ = 0 W

Analog System Dynamic Contribution—P_{AB}

Operating Mode

P_{AB} = PAC20

Standby Mode and Sleep Mode

P_{AB} = 0 W

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that the net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100%, as all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
  – Bit 0 (LSB) = 100%
  – Bit 1 = 50%
  – Bit 2 = 25%
  – …
  – Bit 7 (MSB) = 0.78125%
  – Average toggle rate = (100% + 50% + 25% + 12.5% + . . . 0.78125%) / 8.

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When non-tristate output buffers are used, the enable rate should be 100%.

***Table 3-16* • Toggle Rate Guidelines Recommended for Power Calculation**

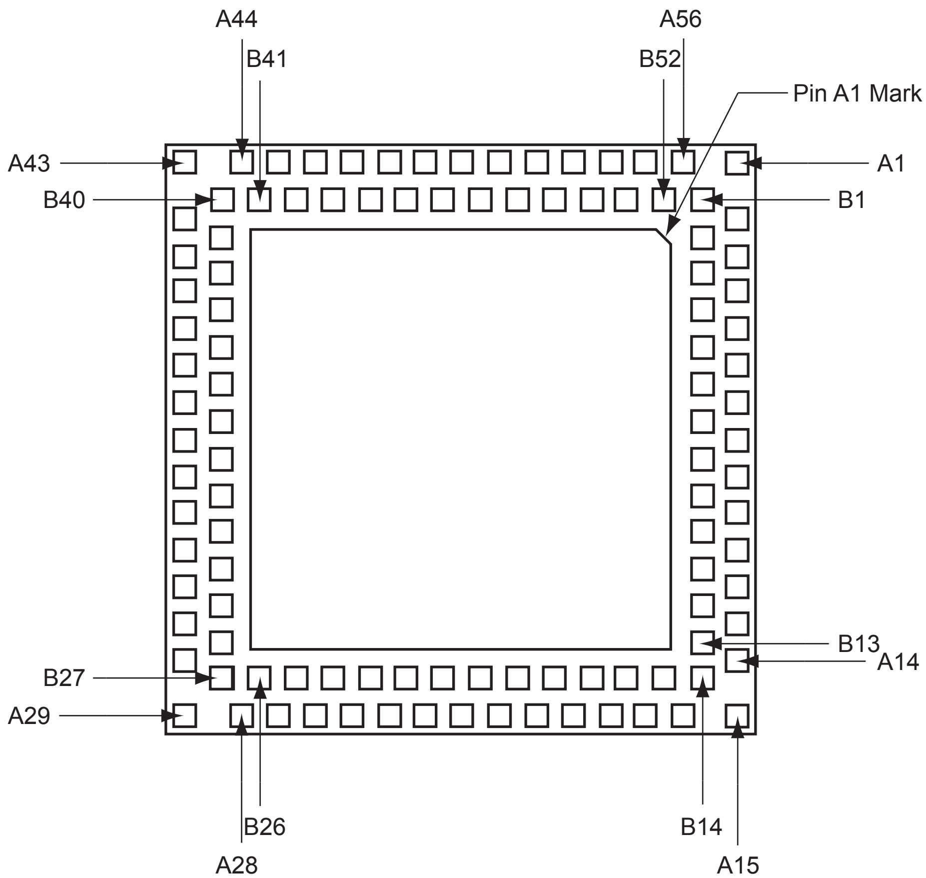
Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

***Table 3-17* • Enable Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%
β_4	NVM enable rate for read operations	0%

4 – Package Pin Assignments

QN108



Note: The die attach paddle center of the package is tied to ground (GND).

Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/default.aspx.

FG676	
Pin Number	AFS1500 Function
R21	IO72NDB2V0
R22	IO72PDB2V0
R23	GND
R24	IO71PDB2V0
R25	VCCIB2
R26	IO67NDB2V0
T1	GND
T2	NC
T3	GFA1/IO105PDB4V0
T4	GFA0/IO105NDB4V0
T5	IO101NDB4V0
T6	IO96PDB4V0
T7	IO96NDB4V0
T8	IO99NDB4V0
T9	IO97NDB4V0
T10	VCCIB4
T11	VCC
T12	GND
T13	VCC
T14	GND
T15	VCC
T16	GND
T17	VCCIB2
T18	IO83NDB2V0
T19	IO78NDB2V0
T20	GDA1/IO81PDB2V0
T21	GDB1/IO80PDB2V0
T22	IO73NDB2V0
T23	IO73PDB2V0
T24	IO71NDB2V0
T25	NC
T26	GND
U1	NC
U2	NC
U3	IO102PDB4V0
U4	IO102NDB4V0

FG676	
Pin Number	AFS1500 Function
U5	VCCIB4
U6	IO91PDB4V0
U7	IO91NDB4V0
U8	IO92PDB4V0
U9	GND
U10	GND
U11	VCC33A
U12	GNDA
U13	VCC33A
U14	GNDA
U15	VCC33A
U16	GNDA
U17	VCC
U18	GND
U19	IO74NDB2V0
U20	GDA0/IO81NDB2V0
U21	GDB0/IO80NDB2V0
U22	VCCIB2
U23	IO75NDB2V0
U24	IO75PDB2V0
U25	NC
U26	NC
V1	NC
V2	VCCIB4
V3	IO100PPB4V0
V4	GND
V5	IO95PDB4V0
V6	IO95NDB4V0
V7	VCCIB4
V8	IO92NDB4V0
V9	GNDNVM
V10	GNDA
V11	NC
V12	AV4
V13	NC
V14	AV5

FG676	
Pin Number	AFS1500 Function
V15	AC5
V16	NC
V17	GNDA
V18	IO77PPB2V0
V19	IO74PDB2V0
V20	VCCIB2
V21	IO82NDB2V0
V22	GDA2/IO82PDB2V0
V23	GND
V24	GDC1/IO79PDB2V0
V25	VCCIB2
V26	NC
W1	GND
W2	IO94PPB4V0
W3	IO98PDB4V0
W4	IO98NDB4V0
W5	GEC1/IO90PDB4V0
W6	GEC0/IO90NDB4V0
W7	GND
W8	VCCNVM
W9	VCCIB4
W10	VCC15A
W11	GNDA
W12	AC4
W13	VCC33A
W14	GNDA
W15	AG5
W16	GNDA
W17	PUB
W18	VCCIB2
W19	TDI
W20	GND
W21	IO84NDB2V0
W22	GDC2/IO84PDB2V0
W23	IO77NPB2V0
W24	GDC0/IO79NDB2V0

5 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each revision of the Fusion datasheet.

Revision	Changes	Page
Revision 6 (March 2014)	Note added for the discontinuance of QN108 and QN180 packages to the "Package I/Os: Single-/Double-Ended (Analog)" table and the "Temperature Grade Offerings" table (SAR 55113, PDN 1306).	II and IV
	Updated details about page programming time in the "Program Operation" section (SAR 49291).	2-46
	ADC_START changed to ADCSTART in the "ADC Operation" section (SAR 44104).	2-104
Revision 5 (January 2014)	Calibrated offset values (AFS090, AFS250) of the external temperature monitor in Table 2-49 • Analog Channel Specifications have been updated (SAR 51464).	2-117
	Specifications for the internal temperature monitor in Table 2-49 • Analog Channel Specifications have been updated (SAR 50870).	2-117
Revision 4 (January 2013)	The "Product Ordering Codes" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43177).	III
	The note in Table 2-12 • Fusion CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42563).	2-28
	Table 2-49 • Analog Channel Specifications was modified to update the uncalibrated offset values (AFS250) of the external and internal temperature monitors (SAR 43134).	2-117
	In Table 2-57 • Prescaler Control Truth Table—AV (x = 0), AC (x = 1), and AT (x = 3), changed the column heading from 'Full-Scale Voltage' to 'Full Scale Voltage in 10-Bit Mode', and added and updated Notes as required (SAR 20812).	2-130
	The values for the Speed Grade (-1 and Std.) for FDDRIMAX (Table 2-180 • Input DDR Propagation Delays) and values for the Speed Grade (-2 and Std.) for FDDOMAX (Table 2-182 • Output DDR Propagation Delays) had been inadvertently interchanged. This has been rectified (SAR 38514).	2-220, 2-222
	Added description about what happens if a user connects VAREF to an external 3.3 V on their board to the "VAREF Analog Reference Voltage" section (SAR 35188).	2-225
	Added a note to Table 3-2 • Recommended Operating Conditions1 (SAR 43429): The programming temperature range supported is $T_{ambient}$ = 0°C to 85°C.	3-3
	Added the Package Thermal details for AFS600-PQ208 and AFS250-PQ208 to Table 3-6 • Package Thermal Resistance (SAR 37816). Deleted the Die Size column from the table (SAR 43503).	3-7
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 42495). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 3 (August 2012)	Microblade U1AFS250 and U1AFS1500 devices were added to the product tables.	I – IV
	A sentence pertaining to the analog I/Os was added to the "Specifying I/O States During Programming" section (SAR 34831).	1-9